Silicon NPN Power Transistors 2SC1212 2SC1212A

DESCRIPTION

・With TO-126 package
・Complement to type 2SA743/743A

APPLICATIONS

・For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

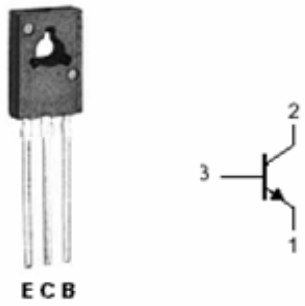

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC1212	Open emitter	50	V
		2SC1212A		80	
V_{CEO}	Collector- emitter voltage	2SC1212	Open base	50	V
		2SC1212A		80	
V_{EBO}	Emitter-base voltage		Open collector	4	V
I_C	Collector current			1	A
P_D	Total power dissipation		T_a=25℃	0.75	W
			T_C=25℃	8	
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55～+150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC1212	I_C=10mA ;R_{BE}=∞	50			V
		2SC1212A		80			
$V_{(BR)CBO}$	Collector-base breakdown voltage	2SC1212	I_C=1mA ;I_E=0	50			V
		2SC1212A		80			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		I_E=1mA ;I_C=0	4			V
V_{CEsat}	Collector-emitter saturation voltage		I_C=1A ;I_B=0.1A			1.5	V
V_{BE}	Base-emitter voltage		I_C=50mA ; V_{CE}=4V			1.0	V
I_{CBO}	Collector cut-off current		V_{CB}=50V; I_E=0			5	μA
h_{FE-1}	DC current gain		I_C=50mA ; V_{CE}=4V	60		200	
h_{FE-2}	DC current gain		I_C=1A ; V_{CE}=4V	20			
f_T	Transition frequency		I_C=30mA ; V_{CE}=4V		160		MHz

◆ **h_{FE-1} Classifications**

B	C
60-120	100-200

PACKAGE OUTLINE

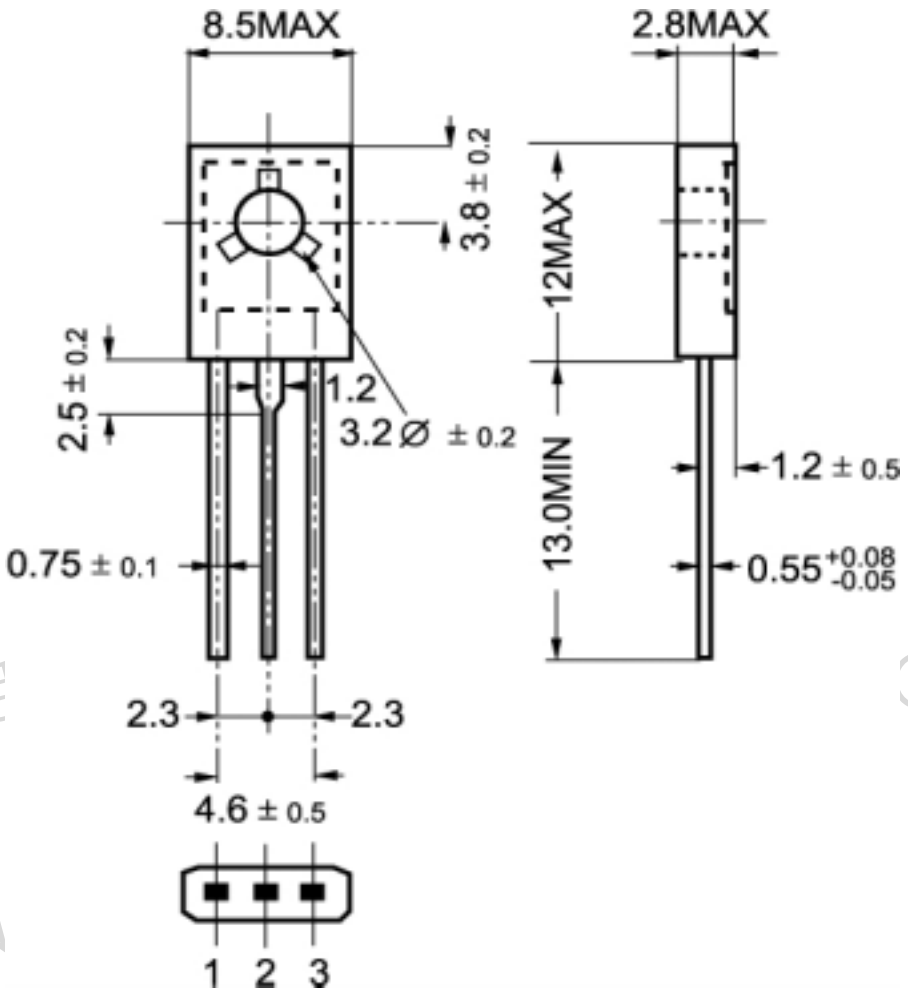

Fig.2 Outline dimensions

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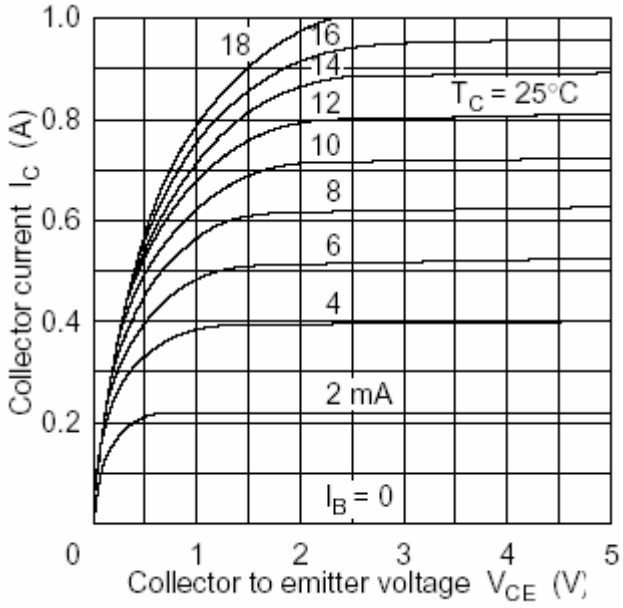

Fig.3 Static Characteristic

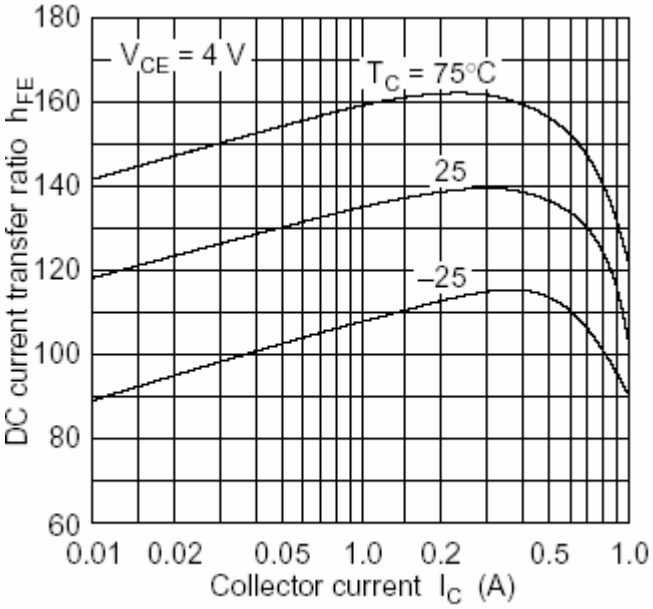

Fig.4 DC current Gain

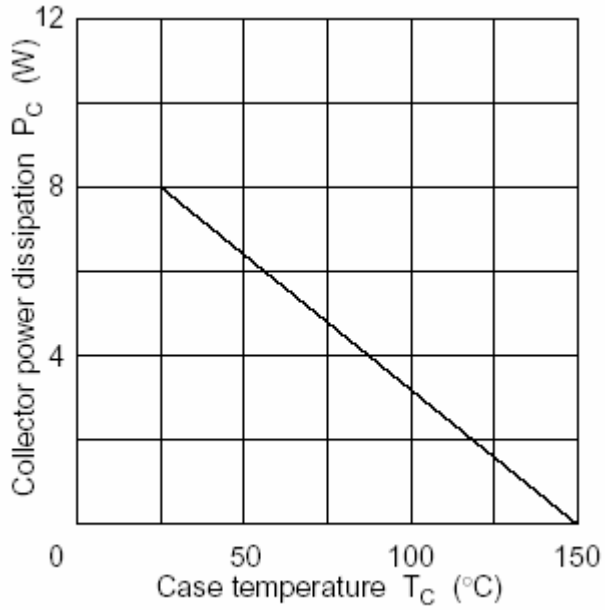

Fig.5 Power Derating